

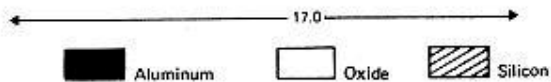
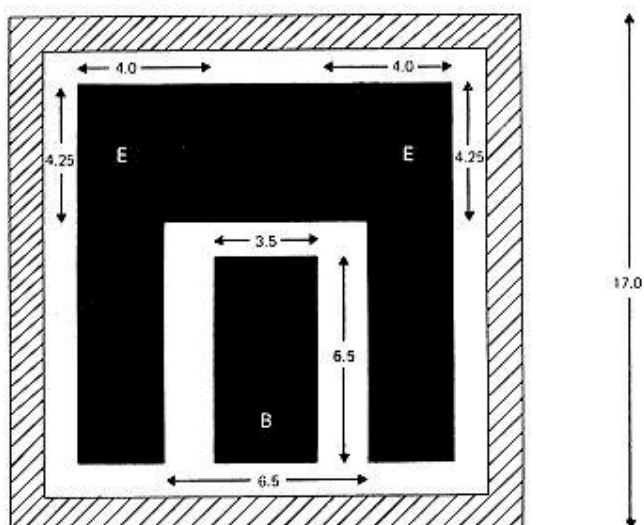
DIONICS INC.

65 RUSHMORE ST., WESTBURY, N.Y. 11590 516-997-7474



2N2222A 2N2221A
2N2219A 2N2218A
2N2222 2N2221
2N2219 2N2218

NPN SILICON
HIGH CURRENT (1.0 AMP) TRANSISTOR CHIPS
DESIGNED FOR HYBRID CIRCUIT APPLICATIONS.



- Chip Thickness=6 Mils \pm 1 Mil
- Min. Dimension Across Bonding Pads=3.5 Mils
- Min. Separation Between Bonding Pads=1.5 Mils
- Distance from Bonding Pads to Edge of Chips=2.5 Mils

Detailed Specifications on Reverse Side

DIONICS INC.

65 RUSHMORE ST., WESTBURY, N.Y. 11590 516-897-7474

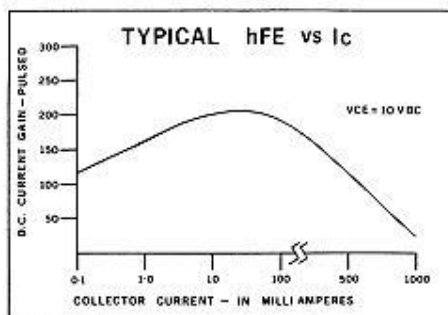


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NPN SILICON
HIGH CURRENT (1.0 AMP) TRANSISTOR CHIPS
DESIGNED FOR HYBRID CIRCUIT APPLICATIONS.

IMPROVED GAIN AT HIGH CURRENT LEVELS • LOW LEAKAGE CHARACTERISTICS •
OVERSIZED BONDING PADS • NO BETA DEGRADATION DURING PROLONGED HIGH
TEMPERATURE ASSEMBLY •

The high efficiency parallel emitter construction provides improved beta retention at high current levels. The large area bonding pads are positioned for maximum flexibility of substrate layout. Unique surface stabilization processing results in lower leakage currents and prevents the beta degradation frequently encountered during the extended high temperature assembly operations required for complex hybrid circuit construction. Chips are gold backed for eutectic die-attach, and have aluminum bonding pads for all conventional wire bonding techniques.



← 100% Probe Tested to These Parameters @ 25°C → Guaranteed →
(tested on sample basis)

h _{FE} @ V _{CE} = 10V				V _{CE0} Volts Min. @ I _C = 10 μA I _E = 0	V _{CE0} Volts Min. @ I _C = 10 mA I _E = 0	V _{CE0} Volts Min. @ I _C = 10 μA I _C = 0	I _{C0} nA Max. @ V _{CE} as below I _E = 0	V _{CE} (SAT.) Volts Max. @ I _C = 150 mA I _E = 15 mA	C ₀₅ pF Max. @ V _{CE} = 10V I _E = 0 f = 100 KHz	f _T MHz Min. @ I _C = 20 mA V _{CE} = 20V f = 100 MHz
@ I _C = 1 mA	@ I _C = 10 mA	@ I _C = 150 mA								
2N 2222A	50	75	100-	70	40	6	10 @ V _{CE} = 60V	0.4	8	250
2N 2219A	MIN	MIN	300							
2N 2221A	25	35	40-	60	30	5	10 @ V _{CE} = 50V	0.4	8	250
2N 2218A	MIN	MIN	120							
2N 2222	50	75	100-	60	30	5	10 @ V _{CE} = 50V	0.4	8	250
2N 2219	MIN	MIN	300							
2N 2221	25	35	40-	60	30	5	10 @ V _{CE} = 50V	0.4	8	250
2N 2218	MIN	MIN	120							

Dimensional Drawing on Reverse Side

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